



## Inspection and metrology

- Optical inspection
- Thin film characterization
- Electrical characterization
- Advanced techniques (SEM, FIB, AFM)

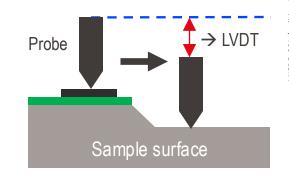
# Optical inspection Summary

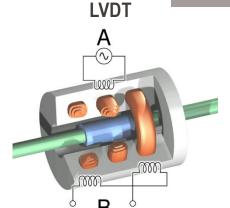
- Easy, fast and cost-effective method for inspection and dimension measurement
- Multiple modes for specific purpose, colour
- Non-contact, non-invasive
- Works for both opaque and transparent specimens
- Workhorse for sample inspection

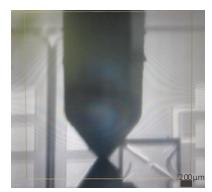
## Mechanical surface profiler

- Diamond probe scans the surface
- Surface height → probe position → electrical signal
- Resolution in Z: ~1nm
- Measurement range in Z: up to 1mm
- Scan length up to 55mm
- Risk to damage the probe or sample

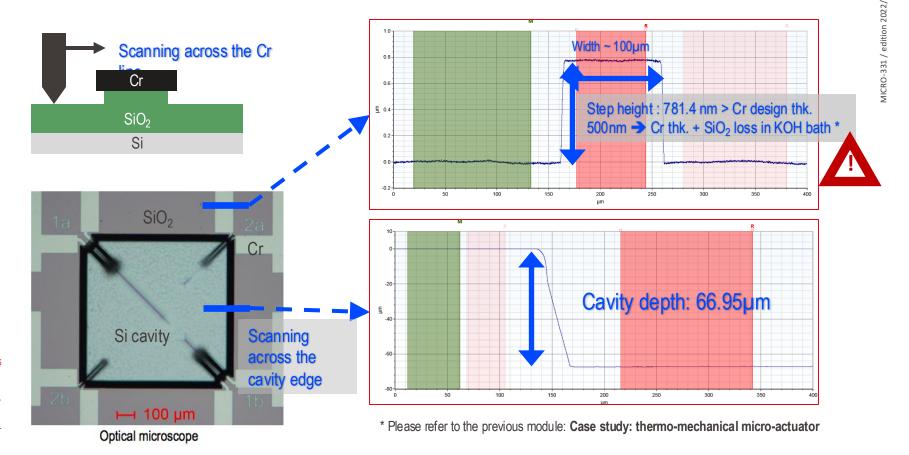
LVDT = linear variable differential transformer







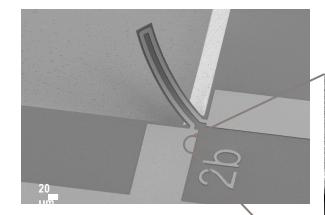
### Surface profile measurement



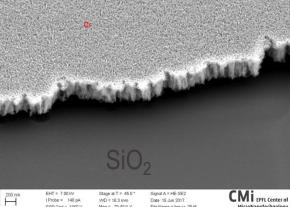
Inspection/Metrology

## Bi-morph surface roughness measurement

measure the surface roughness of Cr and SiO<sub>2</sub>



SEM image of the bi-morph @ 3 keV and 45 degrees tilt



SEM image to indicate where the surface roughness is measured

Atomic Force Microscope: AFM

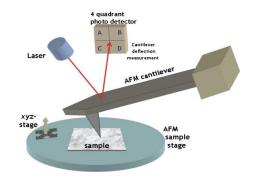


Inspection/Metrology

### 3 types of Microscopes Probing a surface / detecting the reaction







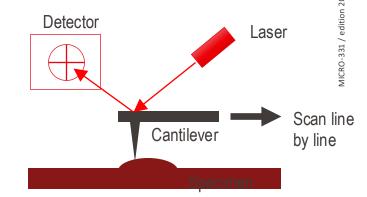
Optical ("light") microscope 'Probe': Light that is reflected from or transmitted through sample.

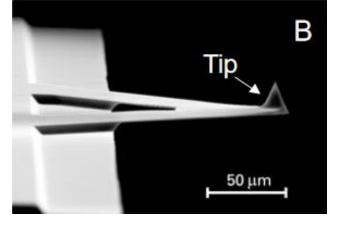
Electron microscope 'Probe': Electrons (shorter wavelength) that are re-emitted from or transmitted through sample. Scanning Probe microscope 'Probe': tip that interacts locally with surface (force, electrons, photons)

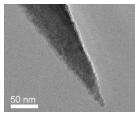


### Atomic force microscopy

- A cantilever probe to touch and scan the surface
- Surface height → probe position → laser signal
- Z resolution: ~ 0.1nm
- XY lateral resolution: < 10nm</li>
- Nano scale 3D surface profile map
- Surface roughness measurement



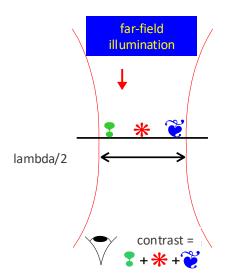




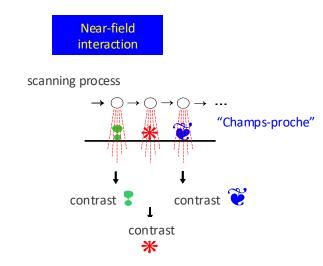
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### Scanning Probe Microscopy

- conventional microscopy
  - wavelength
  - resolution prop. lambda



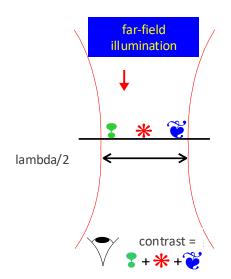
- probe microscopy
  - spatial dimension
  - resolution = f (a,d,...)

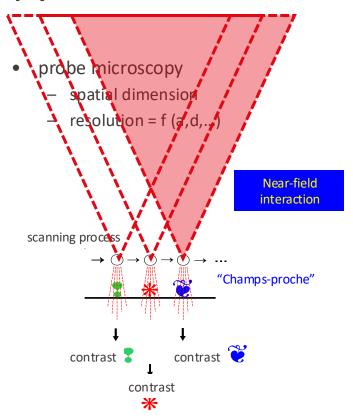


#### EPFL Sca

### Scanning Probe Microscopy

- conventional microscopy
  - wavelength
  - resolution prop. lambda

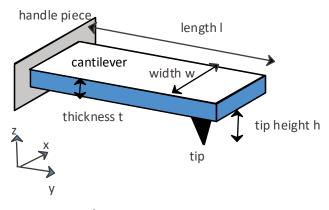




### Microfabrication of cantilevers

- Cantilever = force transducer
- Important parameters
- Spring constant k
- Resonance frequency f
- Practical values
- E: Young's modulus (material constant) E<sub>si</sub> = 1.7 E11 N/m<sup>2</sup>
- I: cross sectional moment of inertia (square cross section I = w t<sup>3</sup>/12)

general Rectangular shape  $k = 3 E I / L^{3}$   $f = \frac{1}{2} \sqrt{\frac{k}{4L^{3}}}$   $k = \frac{Ewt^{3}}{4L^{3}}$ 

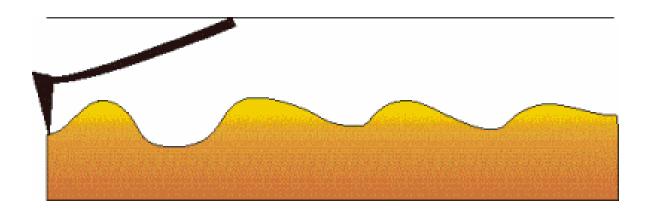


k: 0.01-10 N/m f: > 10kHz

Forces: Micro/nano/pico Newton

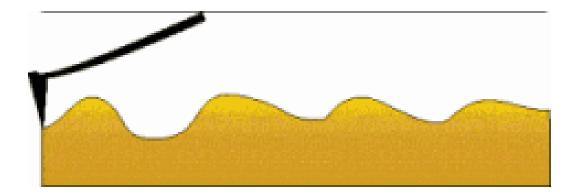
# Contact mode SFM/AFM (constant height)

- Constant height (no z-axis actuation)
- Cantilever is bending
- Contact force is modulated
- Risk of tip and/or sample damage

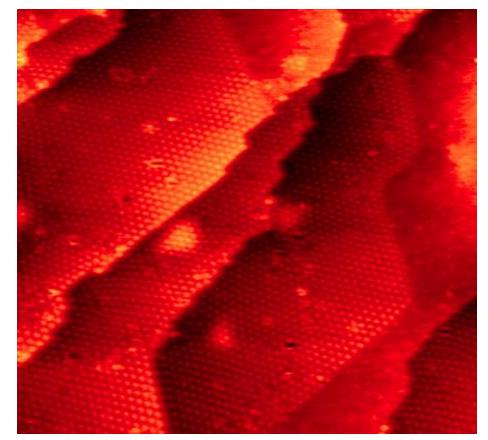


# Contact mode SFM/AFM (constant force)

- Constant force during scanning (z-axes actuation)
- Cantilever bending is constant
- Z-feedback moves sample vs. probe
- Avoid tip damage
- Avoid sample damage
- Important for friction force measurements



## AFM of graphene



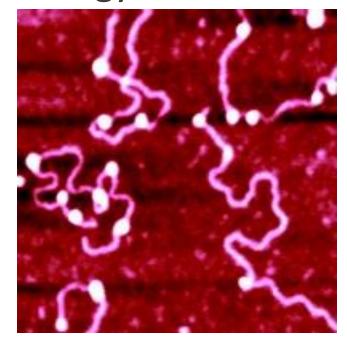
150 nm x 150 nm

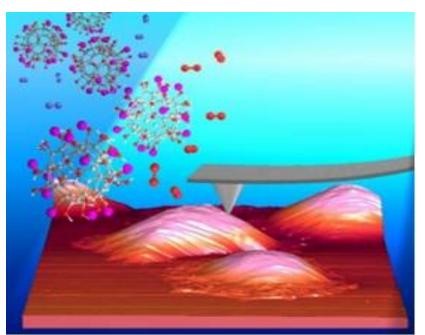
9nm x 9 nm





# Microscopy in biology





DNA molecules

AFM on living cells



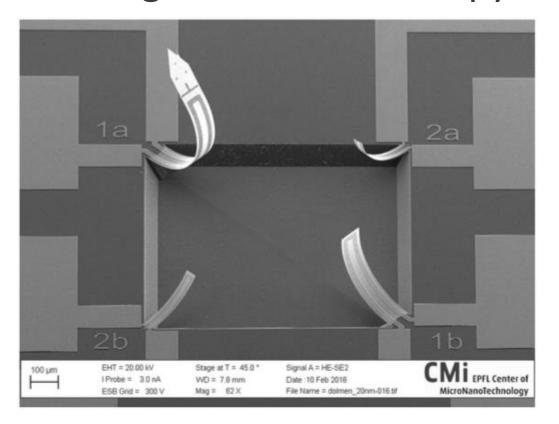
Scanning electron microscopy SEM

 École polytechnique fédérale de Lausanne

MICRO-331 / edition 2022/2023

#### **EPFL**

### Scanning electron microscopy

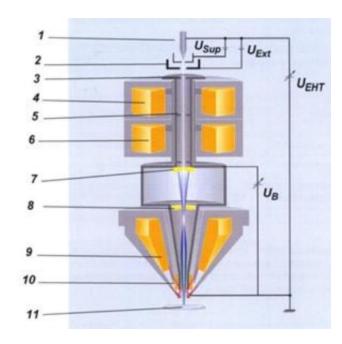


Using electron results in higher resolution compared to visible light

**EPFL** 

# Schematics of SEM system

- System similar to EBL:
  - E-gun: 0.02 30 kV
  - Electromagnetic lenses
  - Vacuum system
- Electrons → detectors → image
- Morphology & compositional analysis
- Resolution: ~1nm
- Accuracy: +/-3%
- Conductive samples required for high quality imaging



Gun	7.	BS
Extractor	8	In-I

3. Anode aperture

. Upper condenser

5. Single hole aperture

6. Lower condenser

BSE detector

In-lens SE detector

Objective lens

). Scanning coils

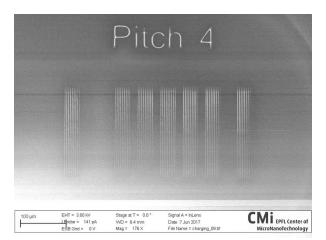
Specimen

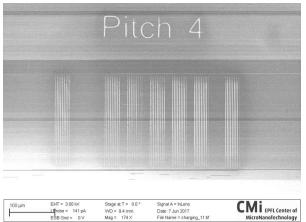
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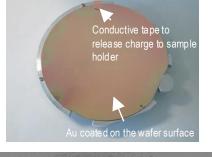
#### **EPFL**

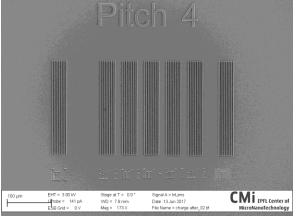
### Charging issue

- Electron charges accumulate on the sample and repulse other electrons if the sample is not conductive
- Solution: metal coating (e.g. 20nm Au) + conductive tape









Poor image due to charging (PR on SiO<sub>2</sub>)

Even worse over time (PR on SiO<sub>2</sub>)

With Au coating



# Focused ion beam FIB

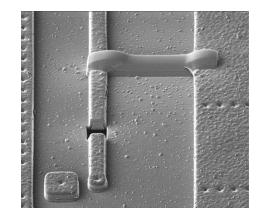
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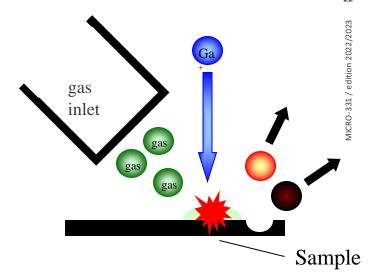
# Access to inner parts of IC



#### **EPFL**

# Gas-Assisted Etching and deposition





Enhanced milling rate

Redeposition is reduced due to volatile reaction products

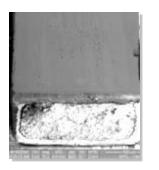
Typical gases: Cl<sub>2</sub>, I<sub>2</sub>, H<sub>2</sub>O, XeF<sub>2</sub>

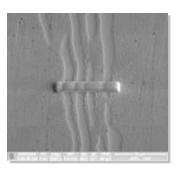
Etch enhancement:

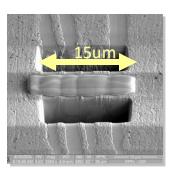
	Si	Al	W	SiO <sub>2</sub>
Cl <sub>2</sub>	7-10	7-10	None	none
XeF <sub>2</sub>	7-12	none	7-10	7-10



## Applications TEM-lamellas and Lift-out













TEM grid, 3mm diameter